

SMF Series



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power Dissipation at $T_A=25^\circ\text{C}$ by $10 \times 1000\mu\text{s}$ (Note 1)	P_{PPM}	200	W
Thermal Resistance Junction- to-Ambient	R_{THJA}	220	$^\circ\text{C/W}$
Thermal Resistance Junction- to-Lead	R_{THJL}	100	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Notes:

1. Non-repetitive current pulse, per Fig. 4 and derated above $T_A=25^\circ\text{C}$ per Fig. 3.

Description

The SMF series is designed specifically to protect sensitive electronic equipment from voltage transients induced by lightning and other transient voltage events.

SMF package is 50% smaller in footprint when compare to SMA package and delivering one of the lowest height profiles (1.1mm) in the industry.

Features

- Compatible with industrial standard package SOD-123
- For surface mounted applications to optimize board space
- Low profile: maximum height of 1.1mm.
- Typical failure mode is short from over-specified voltage or current
- Whisker test is conducted based on JEDEC JESD201A per its table 4a and 4c
- IEC-61000-4-2 ESD 15kV(Air), 8kV (Contact)
- ESD protection of data lines in accordance with IEC 61000-4-2 (IEC801-2)
- EFT protection of data lines in accordance with IEC 61000-4-4 (IEC801-4)
- Low inductance, excellent clamping capability
- 200W peak pulsepower capability at $10 \times 1000\mu\text{s}$ waveform, repetition rate (duty cycle): 0.01%
- Fast response time: typically less than 1.0ns from 0 Volts to V_{BR} min
- High temperature soldering: $260^\circ\text{C}/40$ seconds at terminals
- Glass passivated junction
- Built-in strain relief
- Matte tin lead-free plated
- Halogen-free and RoHS compliant

Applications

SMF devices are ideal for the protection of I/O interfaces, V_{CC} bus and other vulnerable circuit used in cellular phones, portable devices, business machines, power supplies and other consumer applications.

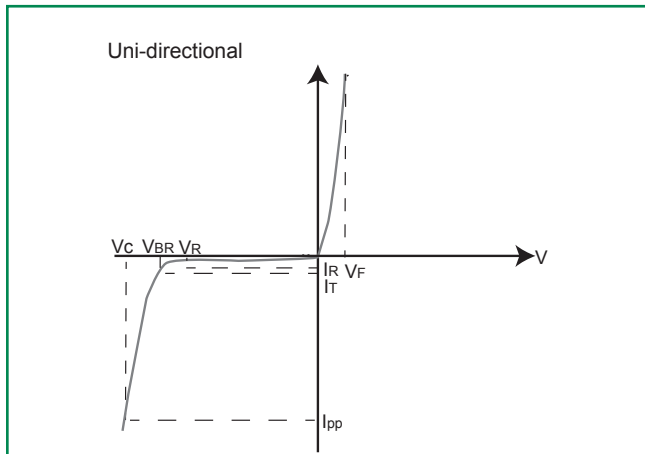
Electrical Characteristics (T_A=25°C unless otherwise noted)

Part Number	Marking	Breakdown Voltage V _{BR} (Volts) @ I _T		Test Current I _T (mA)	Reverse Stand off Voltage V _R (V)	Maximum Reverse Leakage @ V _R I _R (μA)	Maximum Peak Pulse Current I _{PP} (A)	Maximum Clamping Voltage @ I _{PP} V _C (V)
	Code	MIN	MAX					
SMF5.0A	AE	6.4	7.0	10	5.0	400	21.7	9.2
SMF6.0A	AG	6.67	7.37	10	6.0	400	19.4	10.3
SMF6.5A	AK	7.22	7.98	10	6.5	250	17.9	11.2
SMF7.0A	AM	7.78	8.6	10	7.0	100	16.7	12
SMF7.5A	AP	8.33	9.21	1	7.5	50	15.5	12.9
SMF8.0A	AR	8.89	9.83	1	8.0	25	14.7	13.6
SMF8.5A	AT	9.44	10.4	1	8.5	10	13.9	14.4
SMF9.0A	AV	10.0	11.1	1	9.0	5	13	15.4
SMF10A	AX	11.1	12.3	1	10	2.5	11.8	17
SMF11A	AZ	12.2	13.5	1	11	2.5	11	18.2
SMF12A	BE	13.3	14.7	1	12	2.5	10.1	19.9
SMF13A	BG	14.4	15.9	1	13	1.0	9.3	21.5
SMF14A	BK	15.6	17.2	1	14	1.0	8.6	23.2
SMF15A	BM	16.7	18.5	1	15	1.0	8.2	24.4
SMF16A	BP	17.8	19.7	1	16	1.0	7.7	26
SMF17A	BR	18.9	20.9	1	17	1.0	7.2	27.6
SMF18A	BT	20.0	22.1	1	18	1.0	6.8	29.2
SMF20A	BV	22.2	24.5	1	20	1.0	6.2	32.4
SMF22A	BX	24.4	26.9	1	22	1.0	5.6	35.5
SMF24A	BZ	26.7	29.5	1	24	1.0	5.1	38.9
SMF26A	CE	28.9	31.9	1	26	1.0	4.8	42.1
SMF28A	CG	31.1	34.4	1	28	1.0	4.4	45.4
SMF30A	CK	33.3	36.8	1	30	1.0	4.1	48.4
SMF33A	CM	36.7	40.6	1	33	1.0	3.8	53.3
SMF36A	CP	40.0	44.2	1	36	1.0	3.4	58.1
SMF40A	CR	44.4	49.1	1	40	1.0	3.1	64.5
SMF43A	CT	47.8	52.8	1	43	1.0	2.9	69.4
SMF45A	CV	50.0	55.3	1	45	1.0	2.8	72.7
SMF48A	CX	53.3	58.9	1	48	1.0	2.6	77.4
SMF51A	CZ	56.7	62.7	1	51	1.0	2.4	82.4
SMF54A	DE	60.0	66.3	1	54	1.0	2.3	87.1

Notes:

1. V_{BR} measured after I_T applied for 300μs, I_T = square wave pulse or equivalent.
2. Surge current waveform per 10 x 1000μs exponential wave and derated per Fig.2.
3. All terms and symbols are consistent with ANSI/IEEE C62.35.

I-V Curve Characteristics



P_{PPM} Peak Pulse Power Dissipation – Max power dissipation

V_R Stand-off Voltage – Maximum voltage that can be applied to the TVS without operation

V_{BR} Breakdown Voltage – Maximum current that flows through the TVS at a specified test current (I_T)

V_C Clamping Voltage – Peak voltage measured across the suppressor at a specified I_{ppm} (peak impulse current)

I_R Reverse Leakage Current – Current measured at V_R

V_F Forward Voltage Drop for Uni-directional

Ratings and Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Figure 1 - TVS Transients Clamping Waveform

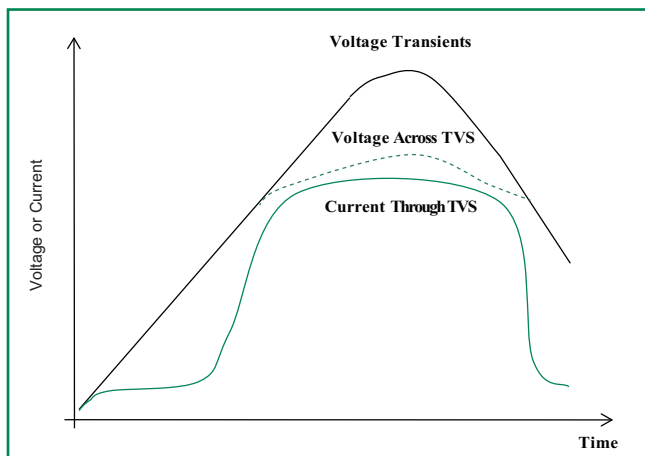
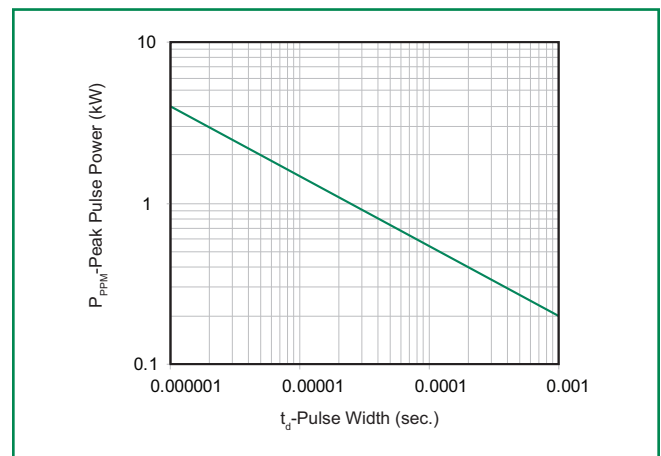


Figure 2 - Peak Pulse Power Rating Curve



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Ratings and Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted) (Continued)

Figure 3 - Pulse Derating Curve

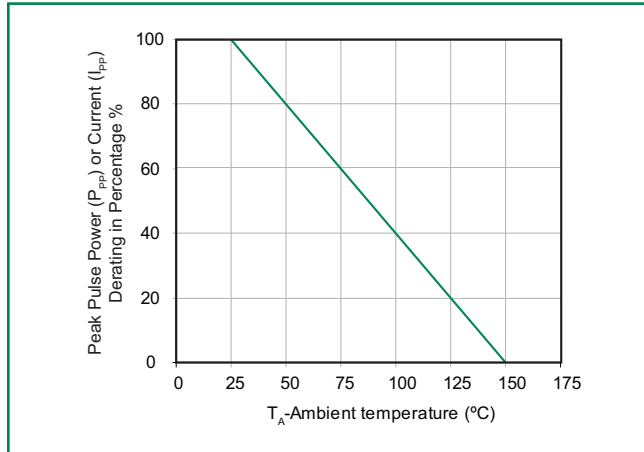


Figure 4 - Pulse Waveform - $10 \times 1000 \mu\text{s}$

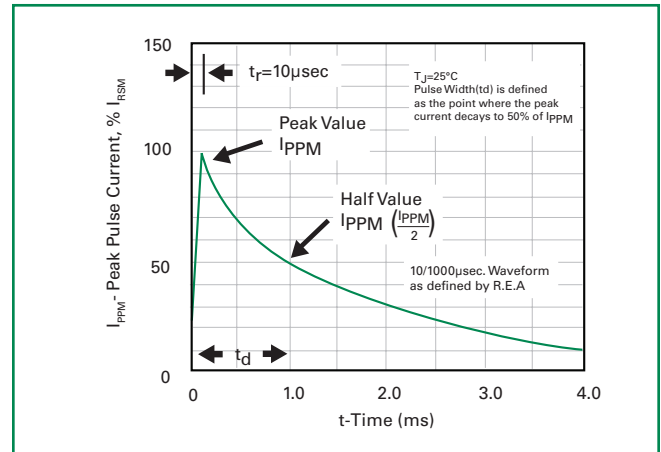


Figure 5 - Steady State Power Dissipation Derating Curve

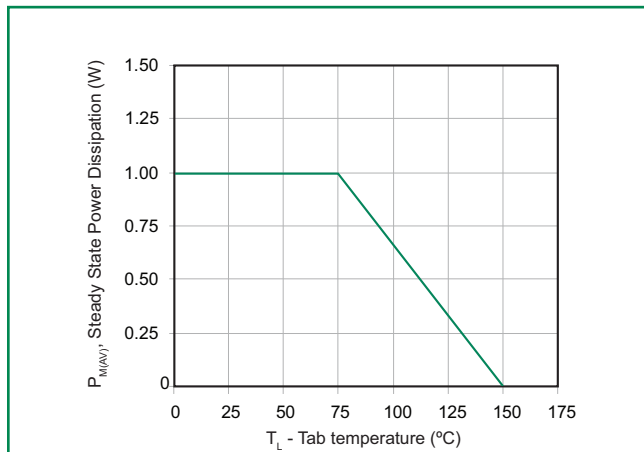


Figure 6 - Forward Voltage

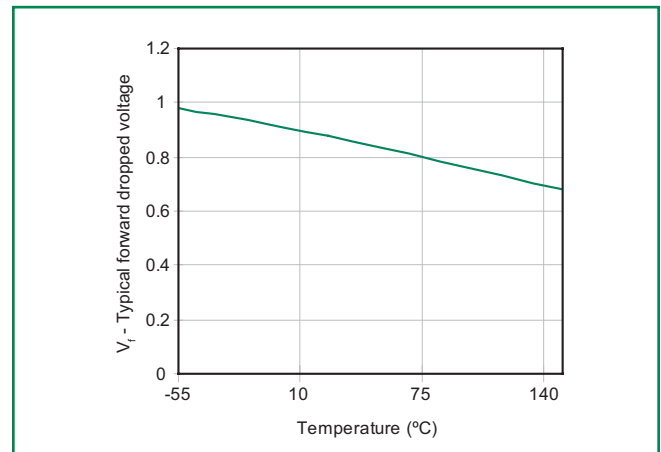
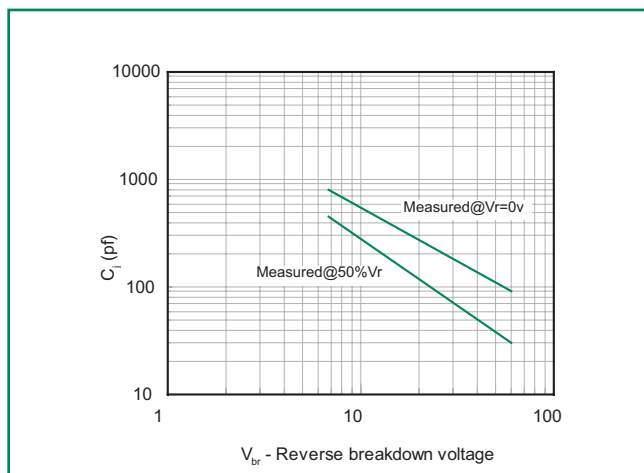
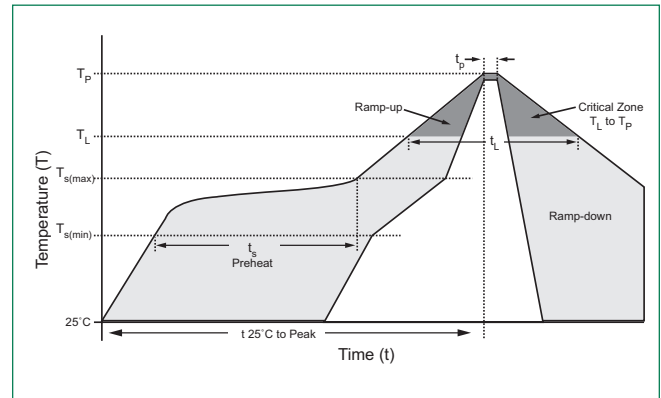


Figure 7 - C_i vs. Working Peak Reverse Voltage



Soldering Parameters

Reflow Condition		Lead-free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (min to max) (t_s)	60 – 150 seconds
Peak Temperature (T_P)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		260°C



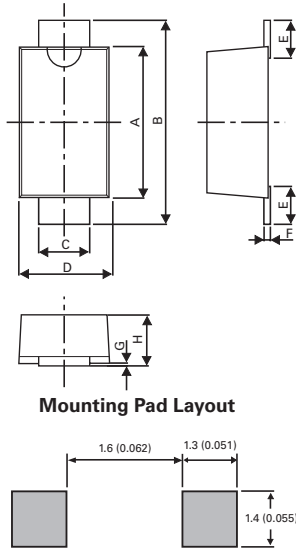
Physical Specifications

Case	SOD-123 plastic over glass passivated junction
Polarity	Color band denotes cathode except bipolar
Terminal	Matte tin-plated leads, solderable per JESD22-B102D

Environmental Specifications

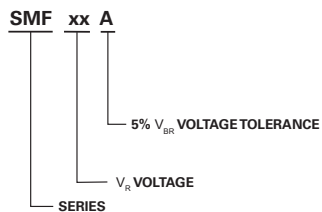
Temperature Cycle	JESD22-A104
Pressure Cooker	JESD22-A102
High Temp. Storage	JESD22-A103
HTRB	JESD22-A108
Thermal Shock	JESD22-A106

Dimensions - SOD-123 Package

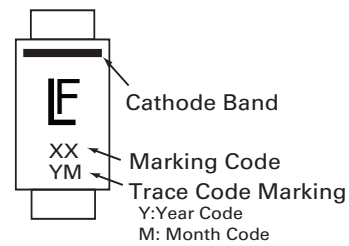


Dimensions	Millimeters		Inches	
	Min	Max	Min	Max
A	2.50	2.90	0.0984	0.1142
B	3.40	3.90	0.1339	0.1535
C	0.70	1.20	0.0275	0.0472
D	1.50	2.00	0.0591	0.0787
E	0.35	0.90	0.0138	0.0354
F	0.05	0.26	0.0020	0.0102
G	0.00	0.10	0.0000	0.0039
H	0.95	1.10	0.0374	0.0433

Part Numbering System



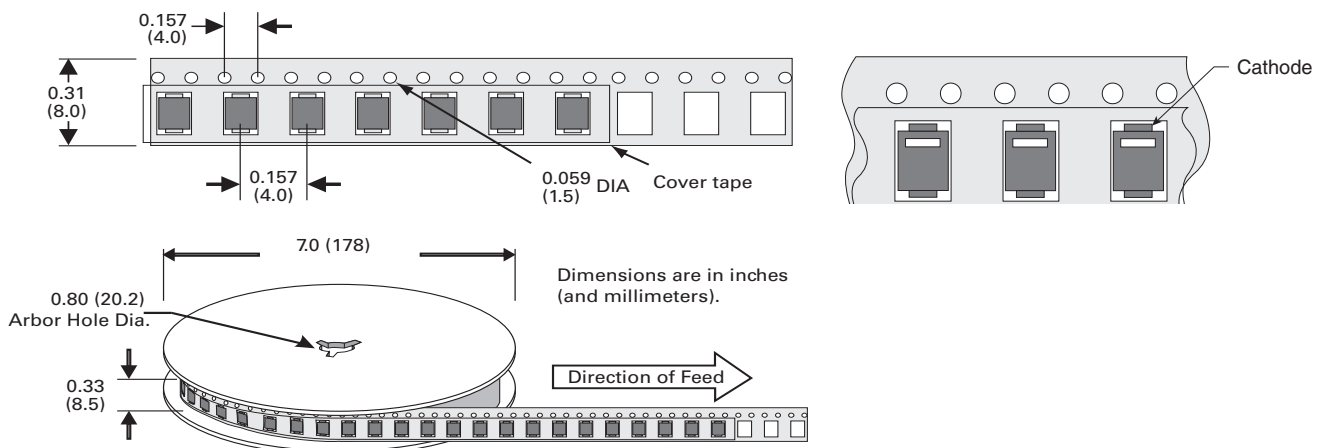
Part Marking System



Packaging

Part number	Component Package	Quantity	Packaging Option	Packaging Specification
SMFXXX	SOD-123	3000	Tape & Reel – 8mm/7" tape	EIA RS-481

Tape and Reel Specification





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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